

Final datasheet

EasyPIM™ module with TRENCHSTOP™ IGBT7 and emitter controlled 7 diode and PressFIT / NTC

Features

- Electrical features
 - $V_{CES} = 1200\text{ V}$
 - $I_{C\text{ nom}} = 15\text{ A} / I_{CRM} = 30\text{ A}$
 - TRENCHSTOP™ IGBT7
 - Overload operation up to 175°C
 - Low $V_{CE,sat}$
 - Suitable Infineon gate drivers can be found under <https://www.infineon.com/gdfinder>
- Mechanical features
 - PressFIT contact technology
 - 2.5 kV AC 1 minute insulation
 - Al_2O_3 substrate with low thermal resistance
 - Compact design
 - High power density



Typical appearance

Potential applications

- Auxiliary inverters
- Motor drives
- Air conditioning

Product validation

- Qualified for industrial applications according to the relevant tests of IEC 60747, 60749 and 60068

Description

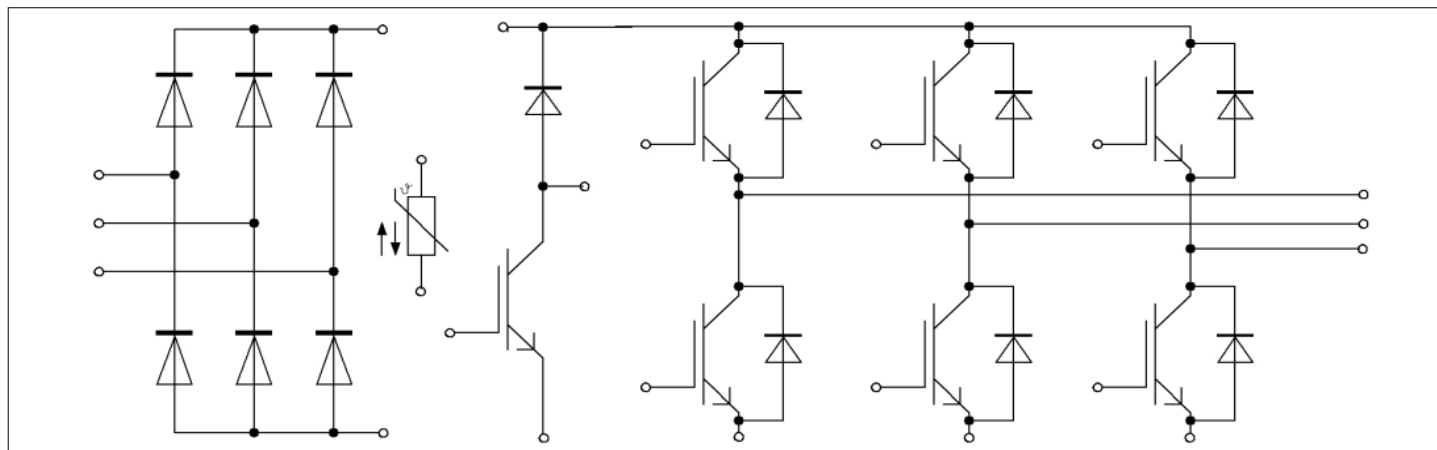


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1 Package

Table 1 Insulation coordination

Parameter	Symbol	Note or test condition	Values	Unit
Isolation test voltage	V_{ISOL}	RMS, $f = 50 \text{ Hz}$, $t = 1 \text{ min}$	2.5	kV
Internal isolation		basic insulation (class 1, IEC 61140)	Al_2O_3	
Comparative tracking index	CTI		> 200	
Relative thermal index (electrical)	RTI	housing	140	°C

Table 2 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Stray inductance module	L_{SCE}			30		nH
Module lead resistance, terminals - chip	$R_{AA'+CC'}$	$T_H = 25 \text{ °C}$, per switch		6		mΩ
Module lead resistance, terminals - chip	$R_{CC'+EE'}$	$T_H = 25 \text{ °C}$, per switch		8		mΩ
Storage temperature	T_{stg}		-40		125	°C
Mounting force per clamp	F		20		50	N
Weight	G			24		g

Note: The current under continuous operation is limited to 25A rms per connector pin.

2 IGBT, Inverter

Table 3 Maximum rated values

Parameter	Symbol	Note or test condition		Values	Unit
Collector-emitter voltage	V_{CES}		$T_{vj} = 25 \text{ °C}$	1200	V
Continuous DC collector current	I_{CDC}	$T_{vj \text{ max}} = 175 \text{ °C}$	$T_H = 125 \text{ °C}$	15	A
Repetitive peak collector current	I_{CRM}	t_p limited by $T_{vj \text{ op}}$		30	A
Gate-emitter peak voltage	V_{GES}			±20	V

Table 4 **Characteristic values**

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Collector-emitter saturation voltage	$V_{CE\ sat}$	$I_C = 15\ A, V_{GE} = 15\ V$	$T_{vj} = 25\ ^\circ C$		1.60	1.85	V
			$T_{vj} = 125\ ^\circ C$		1.74		
			$T_{vj} = 175\ ^\circ C$		1.82		
Gate threshold voltage	V_{GETh}	$I_C = 0.55\ mA, V_{CE} = V_{GE}, T_{vj} = 25\ ^\circ C$		5.15	5.80	6.45	V
Gate charge	Q_G	$V_{GE} = \pm 15\ V, V_{CC} = 600\ V, T_{vj} = 25\ ^\circ C$			0.234		μC
Internal gate resistor	R_{Gint}	$T_{vj} = 25\ ^\circ C$			0		Ω
Input capacitance	C_{ies}	$f = 100\ kHz, T_{vj} = 25\ ^\circ C, V_{CE} = 25\ V, V_{GE} = 0\ V$			2.82		nF
Reverse transfer capacitance	C_{res}	$f = 100\ kHz, T_{vj} = 25\ ^\circ C, V_{CE} = 25\ V, V_{GE} = 0\ V$			0.01		nF
Collector-emitter cut-off current	I_{CES}	$V_{CE} = 1200\ V, V_{GE} = 0\ V$	$T_{vj} = 25\ ^\circ C$			0.003	mA
Gate-emitter leakage current	I_{GES}	$V_{CE} = 0\ V, V_{GE} = 20\ V, T_{vj} = 25\ ^\circ C$				100	nA
Turn-on delay time (inductive load)	t_{don}	$I_C = 15\ A, V_{CC} = 600\ V, V_{GE} = \pm 15\ V, R_{Gon} = 7.5\ \Omega$	$T_{vj} = 25\ ^\circ C$		0.023		μs
			$T_{vj} = 125\ ^\circ C$		0.025		
			$T_{vj} = 175\ ^\circ C$		0.026		
Rise time (inductive load)	t_r	$I_C = 15\ A, V_{CC} = 600\ V, V_{GE} = \pm 15\ V, R_{Gon} = 7.5\ \Omega$	$T_{vj} = 25\ ^\circ C$		0.012		μs
			$T_{vj} = 125\ ^\circ C$		0.015		
			$T_{vj} = 175\ ^\circ C$		0.016		
Turn-off delay time (inductive load)	t_{doff}	$I_C = 15\ A, V_{CC} = 600\ V, V_{GE} = \pm 15\ V, R_{Goff} = 7.5\ \Omega$	$T_{vj} = 25\ ^\circ C$		0.144		μs
			$T_{vj} = 125\ ^\circ C$		0.190		
			$T_{vj} = 175\ ^\circ C$		0.256		
Fall time (inductive load)	t_f	$I_C = 15\ A, V_{CC} = 600\ V, V_{GE} = \pm 15\ V, R_{Goff} = 7.5\ \Omega$	$T_{vj} = 25\ ^\circ C$		0.199		μs
			$T_{vj} = 125\ ^\circ C$		0.301		
			$T_{vj} = 175\ ^\circ C$		0.329		
Turn-on energy loss per pulse	E_{on}	$I_C = 15\ A, V_{CC} = 600\ V, L_\sigma = 35\ nH, V_{GE} = \pm 15\ V, R_{Gon} = 7.5\ \Omega, di/dt = 750\ A/\mu s (T_{vj} = 175\ ^\circ C)$	$T_{vj} = 25\ ^\circ C$		0.87		mJ
			$T_{vj} = 125\ ^\circ C$		1.21		
			$T_{vj} = 175\ ^\circ C$		1.45		
Turn-off energy loss per pulse	E_{off}	$I_C = 15\ A, V_{CC} = 600\ V, L_\sigma = 35\ nH, V_{GE} = \pm 15\ V, R_{Goff} = 7.5\ \Omega, dv/dt = 4000\ V/\mu s (T_{vj} = 175\ ^\circ C)$	$T_{vj} = 25\ ^\circ C$		0.922		mJ
			$T_{vj} = 125\ ^\circ C$		1.44		
			$T_{vj} = 175\ ^\circ C$		1.8		

(table continues...)

Table 4 (continued) Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
SC data	I_{SC}	$V_{GE} \leq 15 \text{ V}, V_{CC} = 800 \text{ V},$ $V_{CEmax}=V_{CES}-L_{sCE} \cdot di/dt$		48		A
		$t_p \leq 8 \mu s,$ $T_{vj}=150 \text{ }^\circ\text{C}$				
		$t_p \leq 7 \mu s,$ $T_{vj}=175 \text{ }^\circ\text{C}$		45		
Thermal resistance, junction to heat sink	R_{thJH}	per IGBT, $\lambda_{grease} = 4.3 \text{ W/(m}\cdot\text{K)}$		1.57		K/W
Temperature under switching conditions	$T_{vj op}$		-40		175	$^\circ\text{C}$

Note: $T_{vj op} > 150^\circ\text{C}$ is allowed for operation at overload conditions. For detailed specifications, please refer to AN 2018-14.

3 Diode, Inverter

Table 5 Maximum rated values

Parameter	Symbol	Note or test condition	Values	Unit
Repetitive peak reverse voltage	V_{RRM}	$T_{vj} = 25 \text{ }^\circ\text{C}$	1200	V
Continuous DC forward current	I_F		15	A
Repetitive peak forward current	I_{FRM}	$t_p = 1 \text{ ms}$	30	A
I^2t - value	I^2t	$t_p = 10 \text{ ms}, V_R = 0 \text{ V}$	$T_{vj} = 125 \text{ }^\circ\text{C}$	A^2s
			$T_{vj} = 175 \text{ }^\circ\text{C}$	
			27.5	
			24	

Table 6 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Forward voltage	V_F	$I_F = 15 \text{ A}, V_{GE} = 0 \text{ V}$	$T_{vj} = 25 \text{ }^\circ\text{C}$		1.98	V
			$T_{vj} = 125 \text{ }^\circ\text{C}$		1.87	
			$T_{vj} = 175 \text{ }^\circ\text{C}$		1.81	
Peak reverse recovery current	I_{RM}	$V_{CC} = 600 \text{ V}, I_F = 15 \text{ A},$ $V_{GE} = -15 \text{ V}, -di_F/dt = 750$ $\text{A}/\mu\text{s} (T_{vj} = 175 \text{ }^\circ\text{C})$	$T_{vj} = 25 \text{ }^\circ\text{C}$		17.7	A
			$T_{vj} = 125 \text{ }^\circ\text{C}$		23.3	
			$T_{vj} = 175 \text{ }^\circ\text{C}$		26.9	

(table continues...)

Table 6 (continued) Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Recovered charge	Q_r	$V_{CC} = 600\text{ V}$, $I_F = 15\text{ A}$, $V_{GE} = -15\text{ V}$, $-di_F/dt = 750\text{ A}/\mu\text{s}$ ($T_{vj} = 175\text{ °C}$)	$T_{vj} = 25\text{ °C}$	1.23		μC
			$T_{vj} = 125\text{ °C}$	1.93		
			$T_{vj} = 175\text{ °C}$	2.71		
Reverse recovery energy	E_{rec}	$V_{CC} = 600\text{ V}$, $I_F = 15\text{ A}$, $V_{GE} = -15\text{ V}$, $-di_F/dt = 750\text{ A}/\mu\text{s}$ ($T_{vj} = 175\text{ °C}$)	$T_{vj} = 25\text{ °C}$	0.342		mJ
			$T_{vj} = 125\text{ °C}$	0.686		
			$T_{vj} = 175\text{ °C}$	1		
Thermal resistance, junction to heat sink	R_{thJH}	per diode, $\lambda_{grease} = 4.3\text{ W}/(\text{m}\cdot\text{K})$		2.51		K/W
Temperature under switching conditions	$T_{vj\text{ op}}$		-40		175	°C

Note: $T_{vj\text{ op}} > 150\text{ °C}$ is allowed for operation at overload conditions. For detailed specifications, please refer to AN 2018-14.

4 Diode, Rectifier

Table 7 Maximum rated values

Parameter	Symbol	Note or test condition		Values	Unit
Repetitive peak reverse voltage	V_{RRM}		$T_{vj} = 25\text{ °C}$	1600	V
Maximum RMS forward current per chip	I_{FRMSM}	$T_H = 100\text{ °C}$		25	A
Maximum RMS current at rectifier output	I_{RMSM}	$T_H = 100\text{ °C}$		25	A
Surge forward current	I_{FSM}	$t_p = 10\text{ ms}$	$T_{vj} = 25\text{ °C}$	300	A
			$T_{vj} = 150\text{ °C}$	245	
I^2t - value	I^2t	$t_p = 10\text{ ms}$	$T_{vj} = 25\text{ °C}$	450	A^2s
			$T_{vj} = 150\text{ °C}$	300	

Table 8 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Forward voltage	V_F	$I_F = 15\text{ A}$ $T_{vj} = 150\text{ °C}$		0.85		V
Reverse current	I_r	$T_{vj} = 150\text{ °C}$, $V_R = 1600\text{ V}$		1		mA
Thermal resistance, junction to heat sink	R_{thJH}	per diode, $\lambda_{grease} = 4.3\text{ W}/(\text{m}\cdot\text{K})$		1.50		K/W

(table continues...)

Table 8 (continued) Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Temperature under switching conditions	$T_{vj, op}$		-40		150	°C

5 IGBT, Brake-Chopper

Table 9 Maximum rated values

Parameter	Symbol	Note or test condition		Values	Unit
Collector-emitter voltage	V_{CES}		$T_{vj} = 25\text{ °C}$	1200	V
Continuous DC collector current	I_{CDC}	$T_{vj\ max} = 175\text{ °C}$	$T_H = 125\text{ °C}$	15	A
Repetitive peak collector current	I_{CRM}	t_p limited by $T_{vj\ op}$		30	A
Gate-emitter peak voltage	V_{GES}			±20	V

Table 10 Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Collector-emitter saturation voltage	$V_{CE\ sat}$	$I_C = 15\text{ A}, V_{GE} = 15\text{ V}$	$T_{vj} = 25\text{ °C}$		1.60	1.85	V
			$T_{vj} = 125\text{ °C}$		1.74		
			$T_{vj} = 175\text{ °C}$		1.82		
Gate threshold voltage	V_{GETh}	$I_C = 0.55\text{ mA}, V_{CE} = V_{GE}, T_{vj} = 25\text{ °C}$		5.15	5.80	6.45	V
Gate charge	Q_G	$V_{GE} = \pm 15\text{ V}, V_{CC} = 600\text{ V}, T_{vj} = 25\text{ °C}$			0.234		μC
Internal gate resistor	R_{Gint}	$T_{vj} = 25\text{ °C}$			0		Ω
Input capacitance	C_{ies}	$f = 100\text{ kHz}, T_{vj} = 25\text{ °C}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$			2.82		nF
Reverse transfer capacitance	C_{res}	$f = 100\text{ kHz}, T_{vj} = 25\text{ °C}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$			0.01		nF
Collector-emitter cut-off current	I_{CES}	$V_{CE} = 1200\text{ V}, V_{GE} = 0\text{ V}$	$T_{vj} = 25\text{ °C}$			0.003	mA
Gate-emitter leakage current	I_{GES}	$V_{CE} = 0\text{ V}, V_{GE} = 20\text{ V}, T_{vj} = 25\text{ °C}$				100	nA
Turn-on delay time (inductive load)	t_{don}	$I_C = 15\text{ A}, V_{CC} = 600\text{ V}, V_{GE} = \pm 15\text{ V}, R_{Gon} = 7.5\text{ Ω}$	$T_{vj} = 25\text{ °C}$		0.023		μs
			$T_{vj} = 125\text{ °C}$		0.025		
			$T_{vj} = 175\text{ °C}$		0.026		

(table continues...)

Table 10 (continued) Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Rise time (inductive load)	t_r	$I_C = 15\text{ A}$, $V_{CC} = 600\text{ V}$, $V_{GE} = \pm 15\text{ V}$, $R_{Gon} = 7.5\ \Omega$	$T_{vj} = 25\text{ °C}$	0.012		μs
			$T_{vj} = 125\text{ °C}$	0.015		
			$T_{vj} = 175\text{ °C}$	0.016		
Turn-off delay time (inductive load)	t_{doff}	$I_C = 15\text{ A}$, $V_{CC} = 600\text{ V}$, $V_{GE} = \pm 15\text{ V}$, $R_{Goff} = 7.5\ \Omega$	$T_{vj} = 25\text{ °C}$	0.144		μs
			$T_{vj} = 125\text{ °C}$	0.190		
			$T_{vj} = 175\text{ °C}$	0.256		
Fall time (inductive load)	t_f	$I_C = 15\text{ A}$, $V_{CC} = 600\text{ V}$, $V_{GE} = \pm 15\text{ V}$, $R_{Goff} = 7.5\ \Omega$	$T_{vj} = 25\text{ °C}$	0.199		μs
			$T_{vj} = 125\text{ °C}$	0.301		
			$T_{vj} = 175\text{ °C}$	0.329		
Turn-on energy loss per pulse	E_{on}	$I_C = 15\text{ A}$, $V_{CC} = 600\text{ V}$, $L_\sigma = 35\text{ nH}$, $V_{GE} = \pm 15\text{ V}$, $R_{Gon} = 7.5\ \Omega$, $di/dt = 750\text{ A}/\mu\text{s}$ ($T_{vj} = 175\text{ °C}$)	$T_{vj} = 25\text{ °C}$	0.87		mJ
			$T_{vj} = 125\text{ °C}$	1.21		
			$T_{vj} = 175\text{ °C}$	1.45		
Turn-off energy loss per pulse	E_{off}	$I_C = 15\text{ A}$, $V_{CC} = 600\text{ V}$, $L_\sigma = 35\text{ nH}$, $V_{GE} = \pm 15\text{ V}$, $R_{Goff} = 7.5\ \Omega$, $dv/dt = 4000\text{ V}/\mu\text{s}$ ($T_{vj} = 175\text{ °C}$)	$T_{vj} = 25\text{ °C}$	0.922		mJ
			$T_{vj} = 125\text{ °C}$	1.44		
			$T_{vj} = 175\text{ °C}$	1.8		
SC data	I_{SC}	$V_{GE} \leq 15\text{ V}$, $V_{CC} = 800\text{ V}$, $V_{CEmax} = V_{CES} - L_{sCE} \cdot di/dt$	$t_p \leq 8\ \mu\text{s}$, $T_{vj} = 150\text{ °C}$	48		A
			$t_p \leq 7\ \mu\text{s}$, $T_{vj} = 175\text{ °C}$	45		
Thermal resistance, junction to heat sink	R_{thJH}	per IGBT, $\lambda_{grease} = 4.3\text{ W}/(\text{m} \cdot \text{K})$		1.54		K/W
Temperature under switching conditions	$T_{vj\text{ op}}$		-40		175	°C

Note: $T_{vj\text{ op}} > 150\text{ °C}$ is allowed for operation at overload conditions. For detailed specifications, please refer to AN 2018-14.

6 Diode, Brake-Chopper

Table 11 Maximum rated values

Parameter	Symbol	Note or test condition	Values	Unit
Repetitive peak reverse voltage	V_{RRM}	$T_{vj} = 25\text{ °C}$	1200	V
Continuous DC forward current	I_F		15	A

(table continues...)

Table 11 (continued) Maximum rated values

Parameter	Symbol	Note or test condition	Values	Unit
Repetitive peak forward current	I_{FRM}	$t_P = 1 \text{ ms}$	30	A
I^2t - value	I^2t	$t_P = 10 \text{ ms}, V_R = 0 \text{ V}$	$T_{vj} = 125^\circ\text{C}$	A^2s
			$T_{vj} = 175^\circ\text{C}$	

Table 12 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Forward voltage	V_F	$I_F = 15 \text{ A}, V_{GE} = 0 \text{ V}$	$T_{vj} = 25^\circ\text{C}$	1.98	2.60	V
			$T_{vj} = 125^\circ\text{C}$	1.87		
			$T_{vj} = 175^\circ\text{C}$	1.81		
Peak reverse recovery current	I_{RM}	$V_{CC} = 600 \text{ V}, I_F = 15 \text{ A}, -di_F/dt = 750 \text{ A}/\mu\text{s}$ ($T_{vj} = 175^\circ\text{C}$)	$T_{vj} = 25^\circ\text{C}$	17.7		A
			$T_{vj} = 125^\circ\text{C}$	23.3		
			$T_{vj} = 175^\circ\text{C}$	26.9		
Recovered charge	Q_r	$V_{CC} = 600 \text{ V}, I_F = 15 \text{ A}, -di_F/dt = 750 \text{ A}/\mu\text{s}$ ($T_{vj} = 175^\circ\text{C}$)	$T_{vj} = 25^\circ\text{C}$	1.23		μC
			$T_{vj} = 125^\circ\text{C}$	1.93		
			$T_{vj} = 175^\circ\text{C}$	2.71		
Reverse recovery energy	E_{rec}	$V_{CC} = 600 \text{ V}, I_F = 15 \text{ A}, -di_F/dt = 750 \text{ A}/\mu\text{s}$ ($T_{vj} = 175^\circ\text{C}$)	$T_{vj} = 25^\circ\text{C}$	0.342		mJ
			$T_{vj} = 125^\circ\text{C}$	0.686		
			$T_{vj} = 175^\circ\text{C}$	1		
Thermal resistance, junction to heat sink	R_{thJH}	per diode, $\lambda_{grease} = 4.3 \text{ W}/(\text{m}\cdot\text{K})$		2.96		K/W
Temperature under switching conditions	$T_{vj\text{op}}$		-40		175	$^\circ\text{C}$

Note: $T_{vj\text{op}} > 150^\circ\text{C}$ is allowed for operation at overload conditions. For detailed specifications, please refer to AN 2018-14.

7 NTC-Thermistor

Table 13 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Rated resistance	R_{25}	$T_{NTC} = 25^\circ\text{C}$		5		k Ω
Deviation of R_{100}	$\Delta R/R$	$T_{NTC} = 100^\circ\text{C}, R_{100} = 493 \Omega$	-5		5	%
Power dissipation	P_{25}	$T_{NTC} = 25^\circ\text{C}$			20	mW

(table continues...)

Table 13 (continued) Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
B-value	$B_{25/50}$	$R_2 = R_{25} \exp[B_{25/50}(1/T_2 - 1/(298,15 \text{ K}))]$		3375		K
B-value	$B_{25/80}$	$R_2 = R_{25} \exp[B_{25/80}(1/T_2 - 1/(298,15 \text{ K}))]$		3411		K
B-value	$B_{25/100}$	$R_2 = R_{25} \exp[B_{25/100}(1/T_2 - 1/(298,15 \text{ K}))]$		3433		K

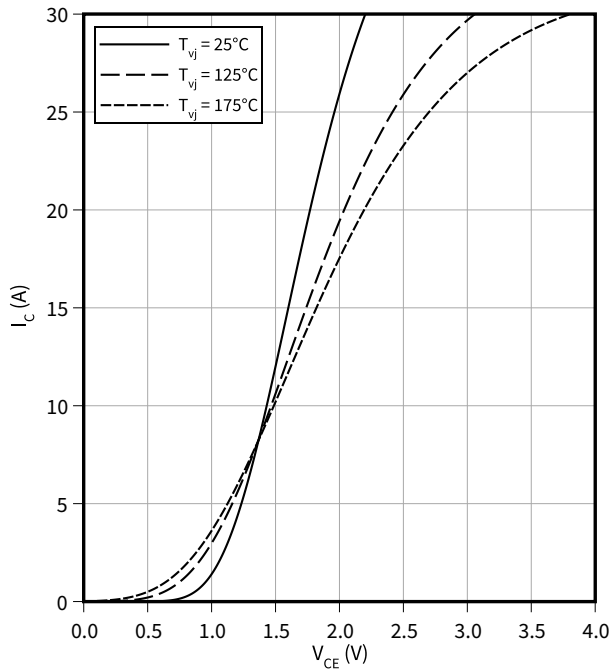
Note: For an analytical description of the NTC characteristics please refer to AN2009-10, chapter 4.

8 Characteristics diagrams

Output characteristic (typical), IGBT, Inverter

$I_C = f(V_{CE})$

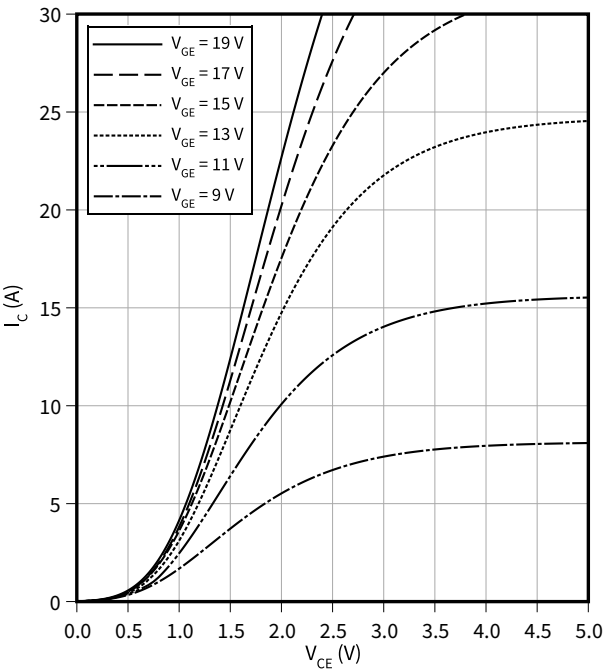
$V_{GE} = 15\text{ V}$



Output characteristic field (typical), IGBT, Inverter

$I_C = f(V_{CE})$

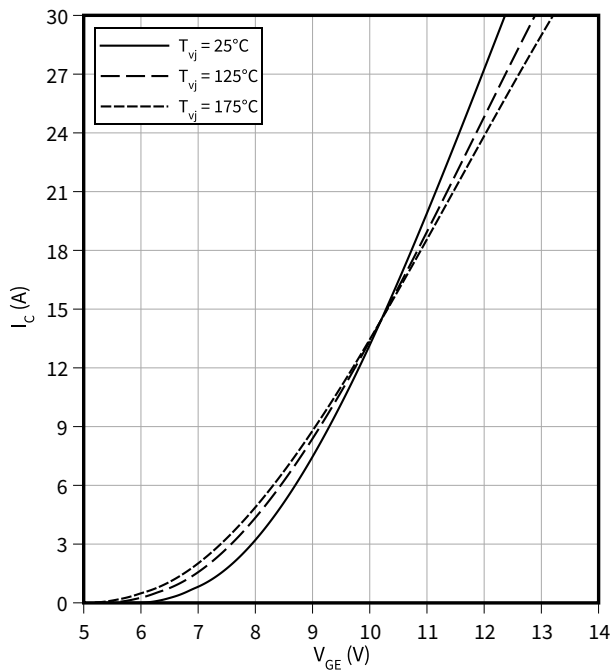
$T_{vj} = 175\text{ °C}$



Transfer characteristic (typical), IGBT, Inverter

$I_C = f(V_{GE})$

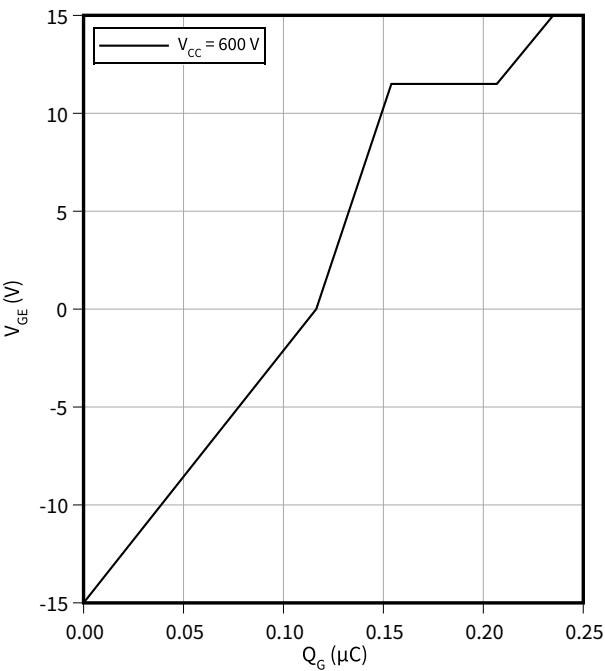
$V_{CE} = 20\text{ V}$



Gate charge characteristic (typical), IGBT, Inverter

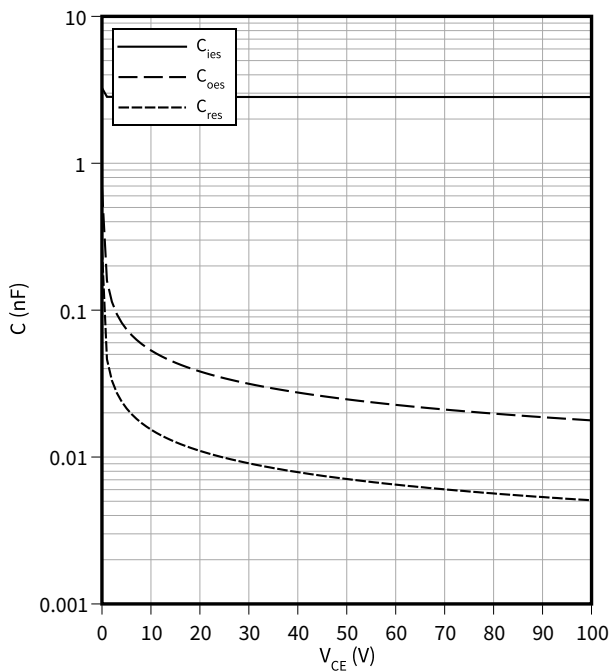
$V_{GE} = f(Q_G)$

$I_C = 15\text{ A}, T_{vj} = 25\text{ °C}$



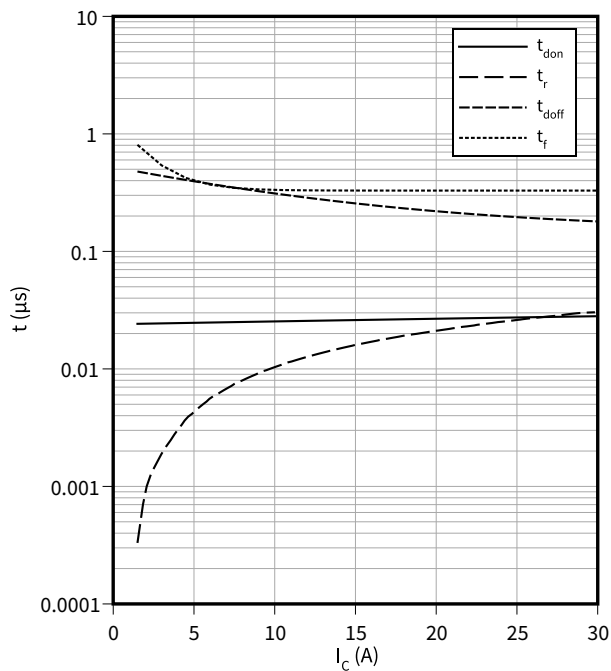
Capacity characteristic (typical), IGBT, Inverter

$C = f(V_{CE})$
 $T_{vj} = 25\text{ °C}, V_{GE} = 0\text{ V}, f = 100\text{ kHz}$



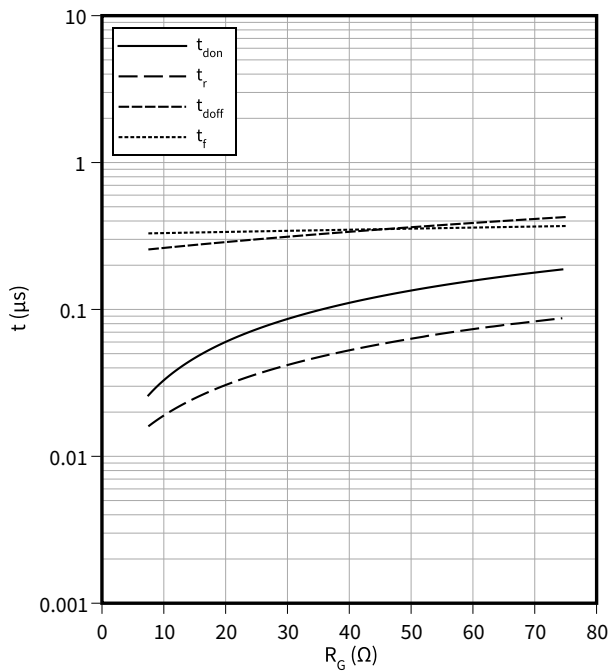
Switching times (typical), IGBT, Inverter

$t = f(I_C)$
 $R_{Goff} = 7.5\text{ }\Omega, R_{Gon} = 7.5\text{ }\Omega, V_{GE} = \pm 15\text{ V}, V_{CC} = 600\text{ V}, T_{vj} = 175\text{ °C}$



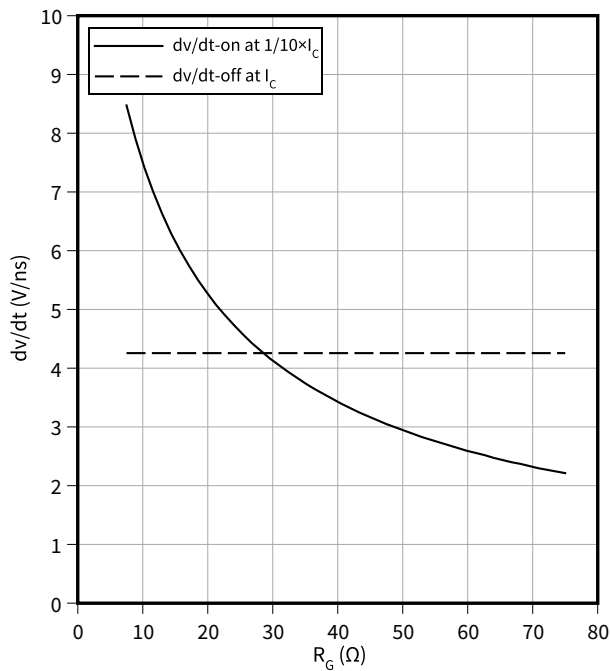
Switching times (typical), IGBT, Inverter

$t = f(R_G)$
 $I_C = 15\text{ A}, V_{CC} = 600\text{ V}, T_{vj} = 175\text{ °C}, V_{GE} = \pm 15\text{ V}$



Voltage slope (typical), IGBT, Inverter

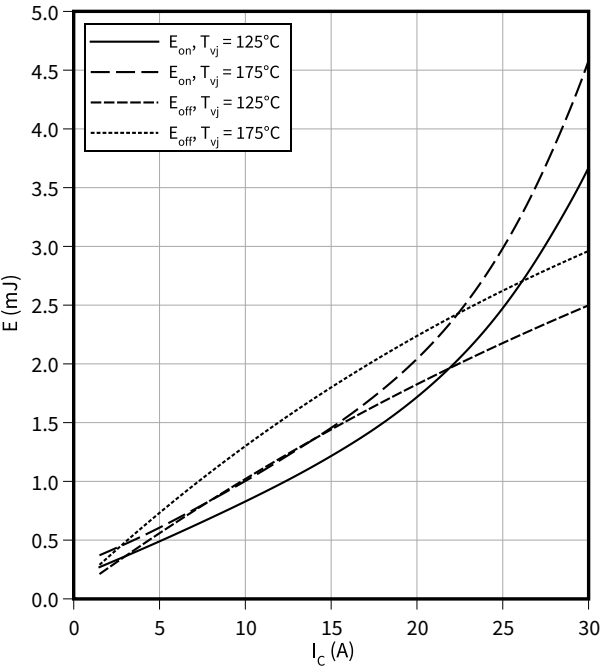
$dv/dt = f(R_G)$
 $V_{GE} = \pm 15\text{ V}, I_C = 15\text{ A}, V_{CC} = 600\text{ V}, T_{vj} = 25\text{ °C}$



8 Characteristics diagrams

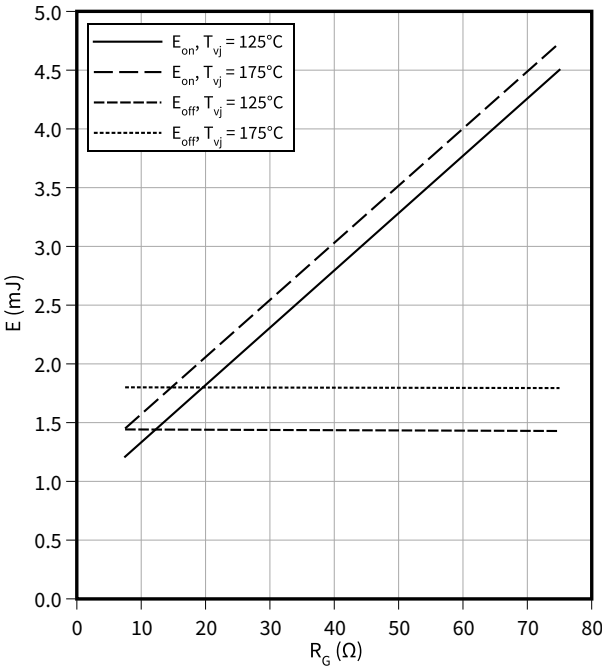
Switching losses (typical), IGBT, Inverter

$E = f(I_C)$
 $R_{Goff} = 7.5 \Omega$, $R_{Gon} = 7.5 \Omega$, $V_{GE} = \pm 15 \text{ V}$, $V_{CC} = 600 \text{ V}$



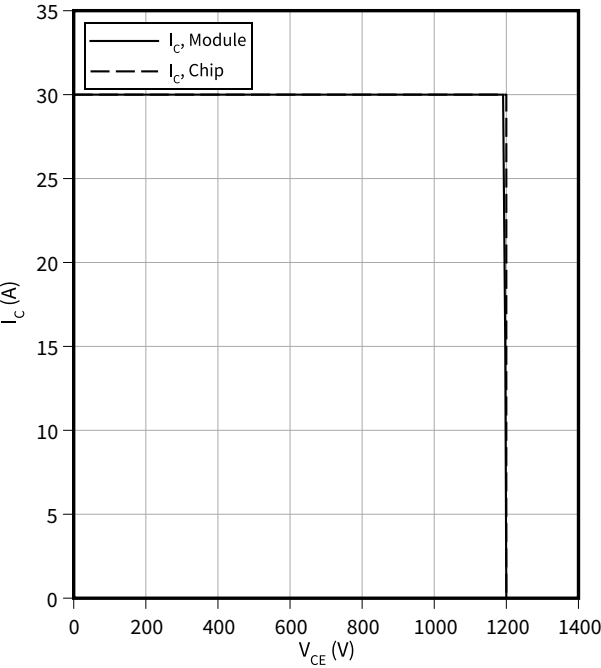
Switching losses (typical), IGBT, Inverter

$E = f(R_G)$
 $V_{GE} = \pm 15 \text{ V}$, $I_C = 15 \text{ A}$, $V_{CC} = 600 \text{ V}$



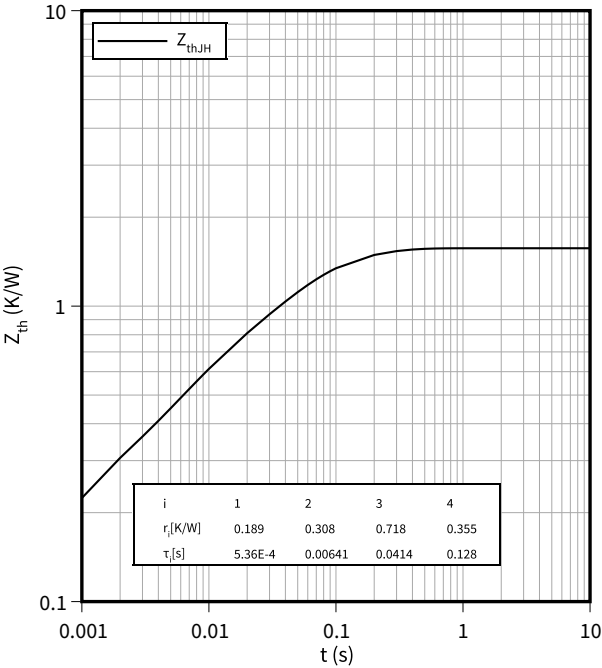
Reverse bias safe operating area (RBSOA), IGBT, Inverter

$I_C = f(V_{CE})$
 $R_{Goff} = 7.5 \Omega$, $V_{GE} = \pm 15 \text{ V}$, $T_{vj} = 175 \text{ }^\circ\text{C}$



Transient thermal impedance, IGBT, Inverter

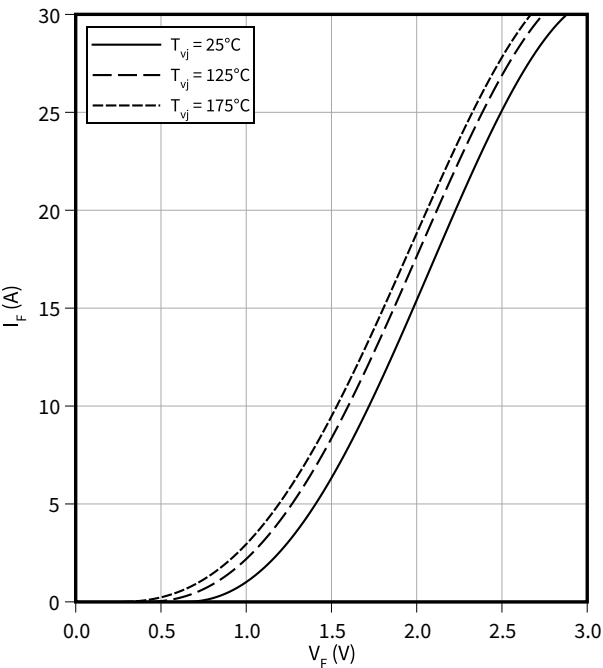
$Z_{th} = f(t)$



8 Characteristics diagrams

Forward characteristic (typical), Diode, Inverter

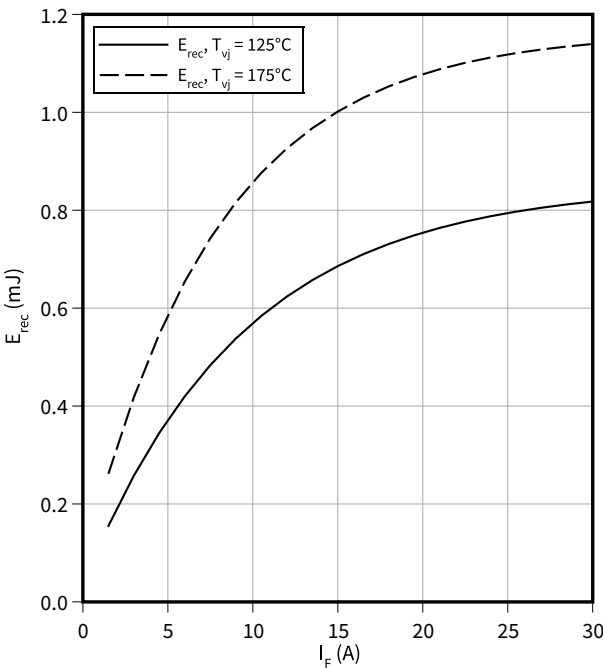
$I_F = f(V_F)$



Switching losses (typical), Diode, Inverter

$E_{rec} = f(I_F)$

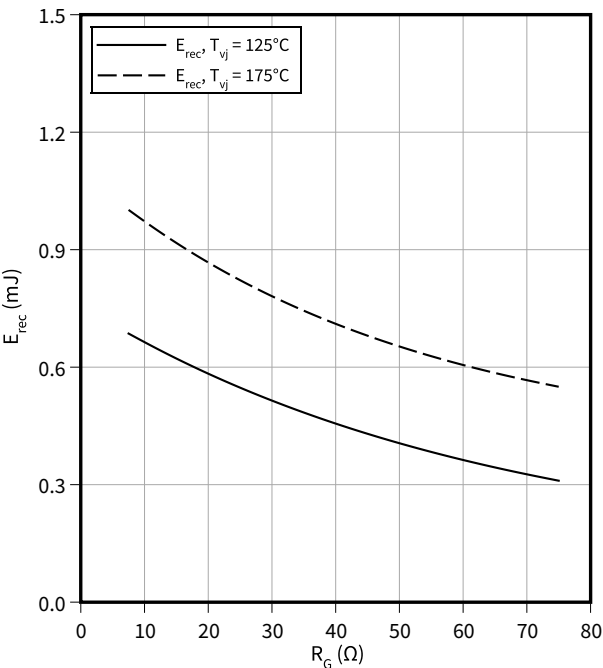
$R_{Gon} = 7.5\ \Omega, V_{CC} = 600\ \text{V}$



Switching losses (typical), Diode, Inverter

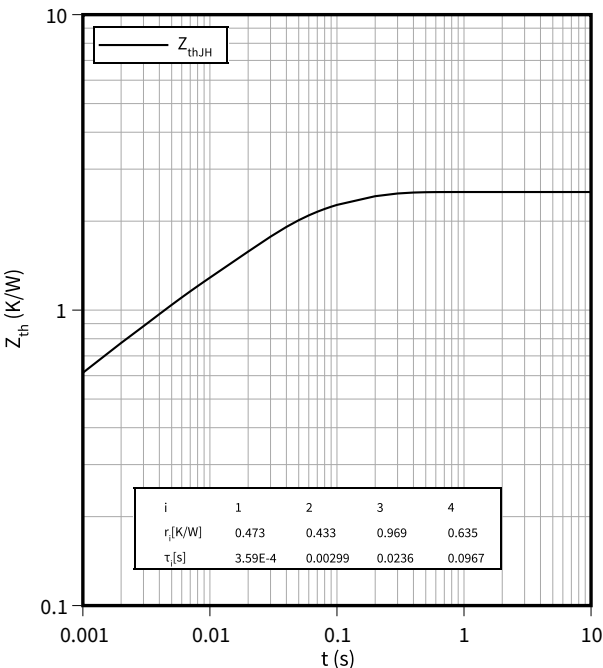
$E_{rec} = f(R_G)$

$I_F = 15\ \text{A}, V_{CC} = 600\ \text{V}$



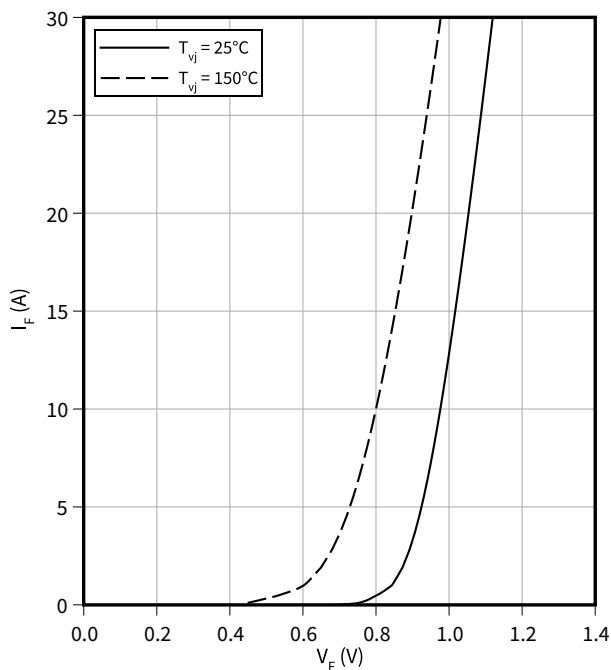
Transient thermal impedance, Diode, Inverter

$Z_{th} = f(t)$



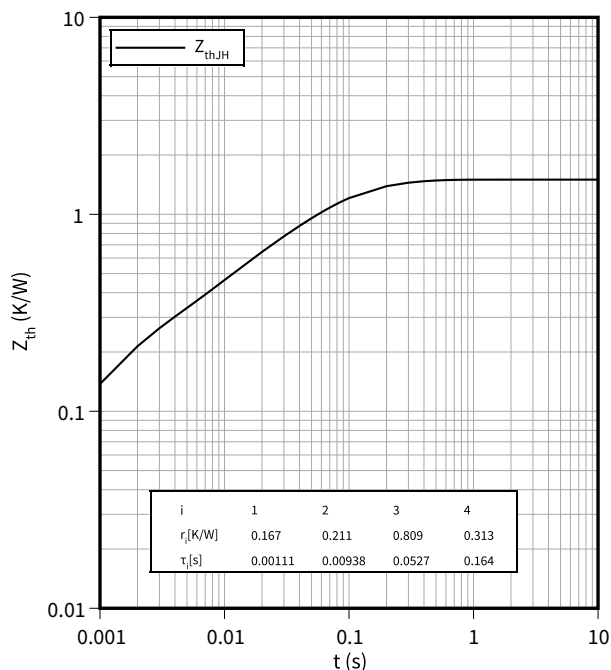
Forward characteristic (typical), Diode, Rectifier

$I_F = f(V_F)$



Transient thermal impedance, Diode, Rectifier

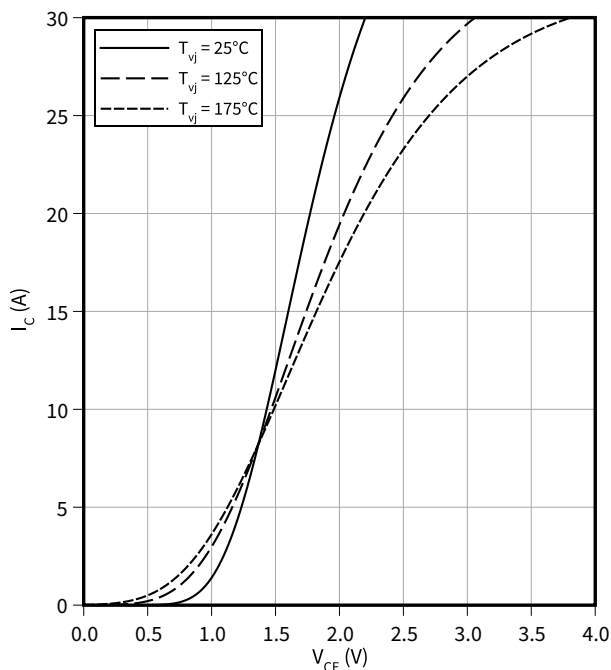
$Z_{th} = f(t)$



Output characteristic (typical), IGBT, Brake-Chopper

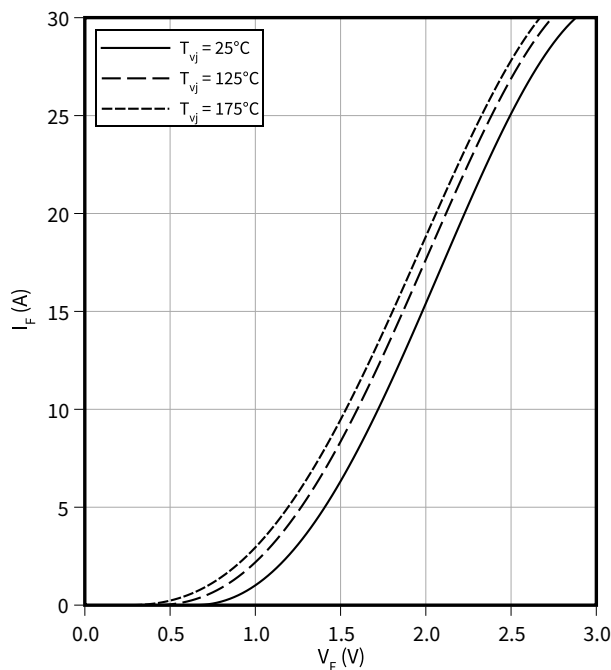
$I_C = f(V_{CE})$

$V_{GE} = 15\text{ V}$



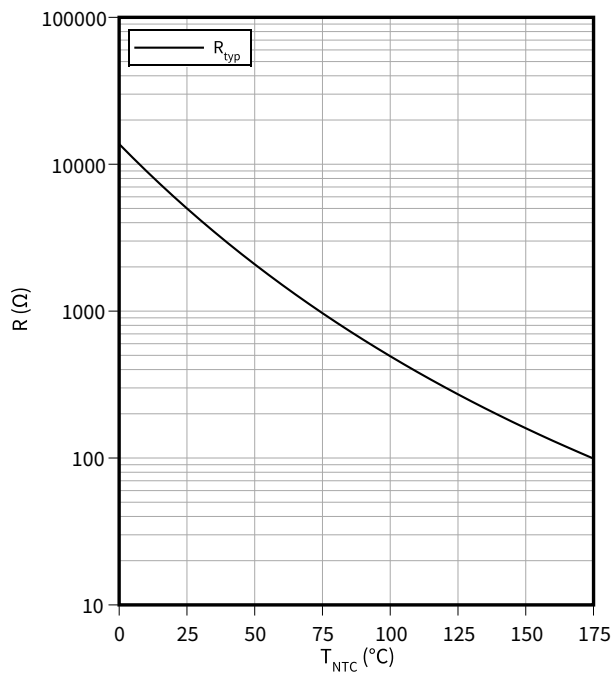
Forward characteristic (typical), Diode, Brake-Chopper

$I_F = f(V_F)$



Temperature characteristic (typical), NTC-Thermistor

$R = f(T_{NTC})$



9 Circuit diagram

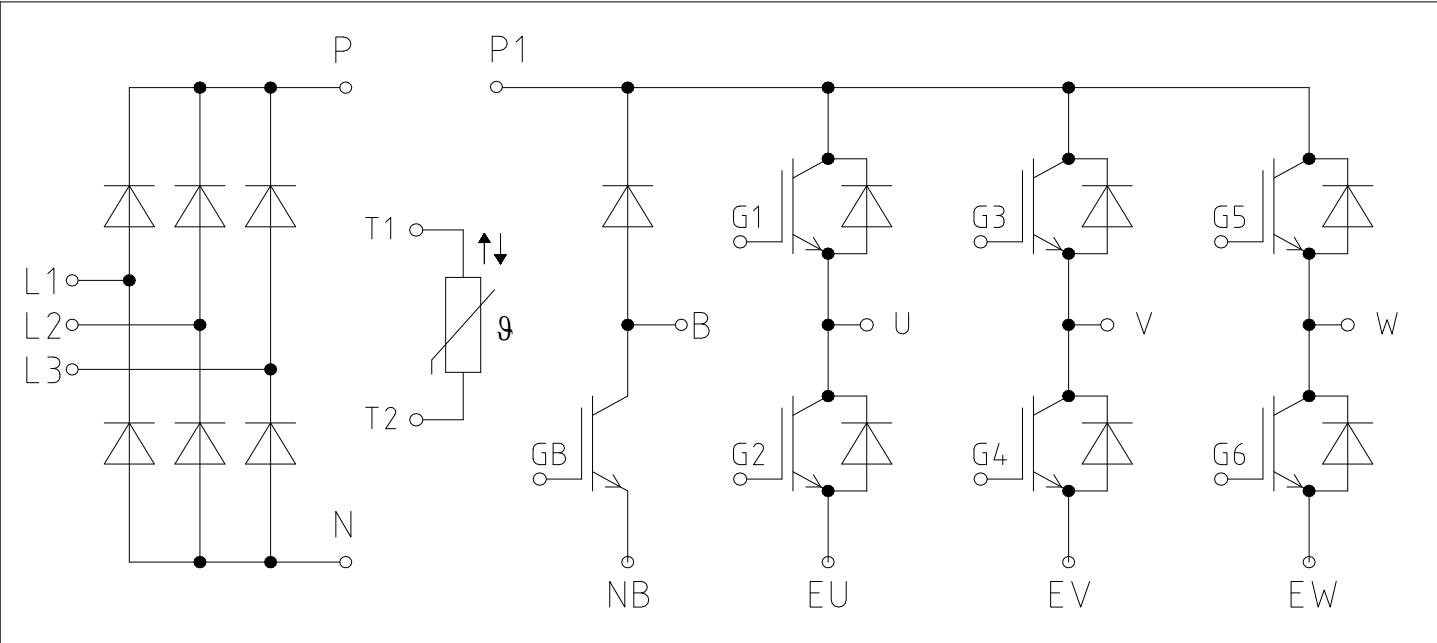


Figure 1

10 Package outlines

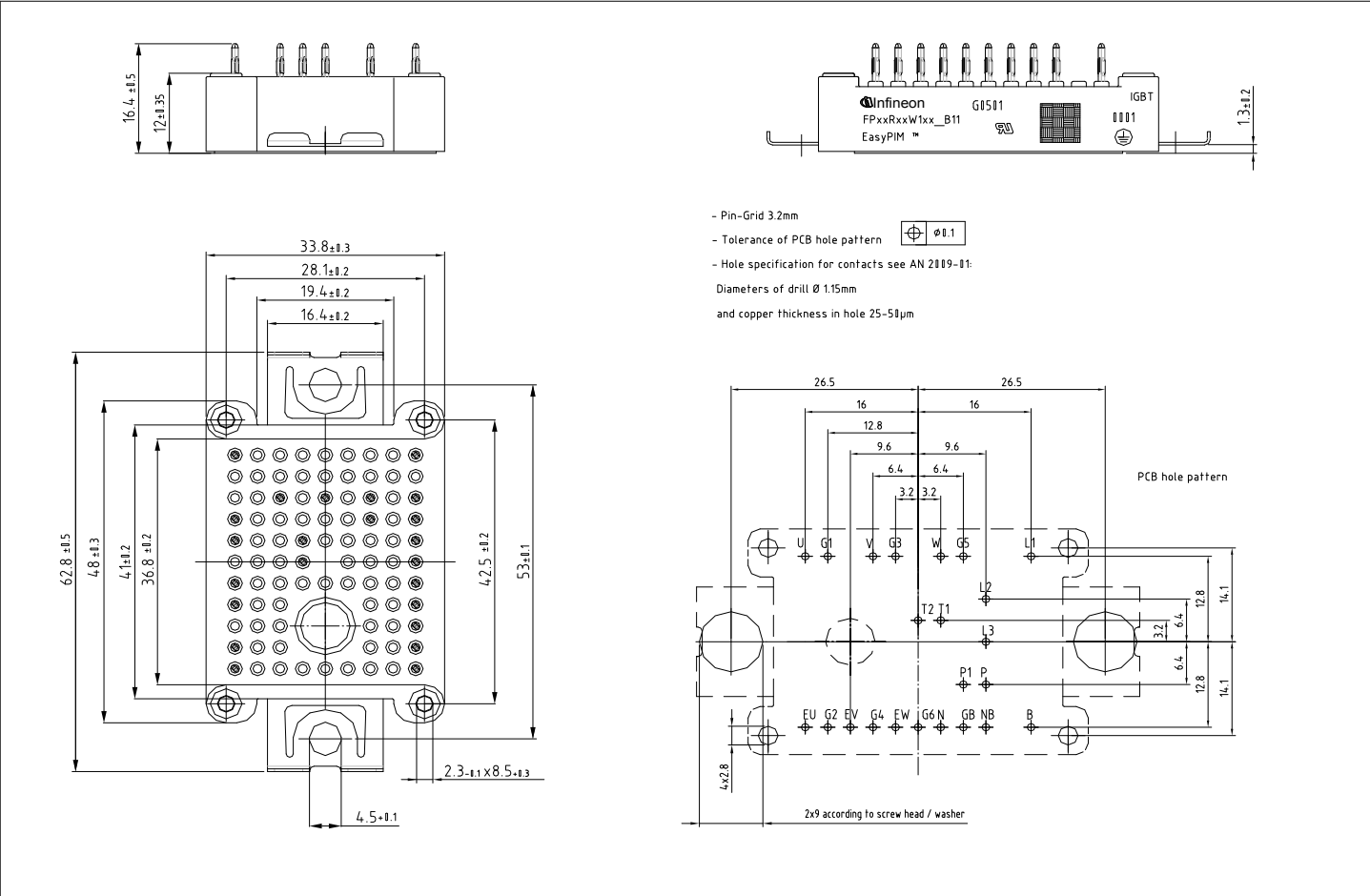


Figure 2

11 Module label code

Module label code			
Code format	Data Matrix		Barcode Code128
Encoding	ASCII text		Code Set A
Symbol size	16x16		23 digits
Standard	IEC24720 and IEC16022		IEC8859-1
Code content	Content	Digit	Example
	Module serial number	1 – 5	71549
	Module material number	6 - 11	142846
	Production order number	12 - 19	55054991
	Date code (production year)	20 – 21	15
	Date code (production week)	22 – 23	30
Example	 71549142846550549911530  71549142846550549911530		

Figure 3

Revision history

Document revision	Date of release	Description of changes
V1.0	2019-01-04	Target datasheet
V2.0	2019-09-19	Preliminary datasheet
n/a	2020-09-01	Datasheet migrated to a new system with a new layout and new revision number schema: target or preliminary datasheet = 0.xy; final datasheet = 1.xy
0.10	2020-12-03	
0.10	2021-03-16	
1.00	2022-12-08	Final datasheet
1.10	2025-07-18	Final datasheet

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